

Docket No.: 57810-084

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277

Nobuhiko HAYASHI, et al. : Confirmation Number:

Serial No.: **Divisional of Appl No. 10/084,050** : Group Art Unit:

Filed: March 10, 2004 : Examiner:

For: NITRIDE-BASED SEMICONDUCTOR ELEMENT AND METHOD OF FORMING
NITRIDE-BASED SEMICONDUCTOR

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The references were cited by or submitted to the U.S. Patent and Trademark Office in parent application Serial No. 10/084,050, filed February 28, 2002, which is relied upon for an

Serial No.:

earlier filing date under 35 USC 120. Thus, copies of these references are not attached. 37 CFR 1.98(d).

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 57810-084		SERIAL NO. Divisional of Appl No. 10/084,050	
				APPLICANT Nobuhiko HAYASHI, et al.			
				FILING DATE March 10, 2004		GROUP	

U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 6,015,979	1/18/2000	Sugiura et al.			
		US 6,051,849	4/18/2000	Davis et al.			
		US 6,503,769	01/07/2003	Nakamura et al.			
		US					
		US					

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
		2000-164989	6/16/2000			Yes	No
		2000-269144	9/29/2000			Japan (w/ English Abstract)	
		2000-21789	1/21/2000			Japan (w/ English Abstract)	
		10-312971	11/24/1998			Japan (w/ English Abstract)	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		S. Nakamura et al., "Long lifetime violet InGaN/GaN/AlGaIn-based semiconductor lasers", Journal of Oyo Denshi Bussei Bunkakai, Vol. 4, (1998), pp. 53-58 and 210-215.	
		Akira Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 36 (1997), pp. L899-L902.	
		Kevin Linthicum et al., "Pendeoepitaxy of gallium nitride thin films", Applied Physics Letter, Vol. 75, No. 2, July 12, 1999, pp. 196-198.	
		Isao Kidoguchi et al., "Air-bridged lateral epitaxial overgrowth of GaN thin films", Applied Physics Letter, Vol. 76, No. 25, June 19, 2000, pp. 3768-3770.	

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.